L Number	Hits	Search Text	DB	Time stamp
1	1	("6277699").PN.	USPAT	2004/06/07 17:20
2	3	(("6091120") or ("5089863") or ("5384479")).PN.	USPAT	2004/06/07 17:21
3	٥ ا	((("6091120") or ("5089863") or	HCDAM	2004/06/07 17 01
	l "	(((6091120") Of ("5089865") Of ("5384479")).PN.) and (tungsten and	USPAT	2004/06/07 17:21
		(hydrogen adj bromide))		
-	3139	438/197.ccls. or 438/299.ccls. or	USPAT	2004/06/07 17:19
	0100	438/301.ccls. or 438/303.ccls. or	OSTAT	2004/00/07 17:19
]		438/305.ccls. or 438/306.ccls.		
-	1871	438/585.ccls. or 438/592.ccls. or	USPAT	2004/06/04 14:43
		438/595.ccls.		2001,00,01 11.43
-	4321	(438/197.ccls. or 438/299.ccls. or	USPAT	2004/06/04 14:43
		438/301.ccls. or 438/303.ccls. or		
		438/305.ccls. or 438/306.ccls.) or		
		(438/585.ccls. or 438/592.ccls. or		
		438/595.ccls.)		
-	85	(()	USPAT	2004/06/04 14:45
		438/301.ccls. or 438/303.ccls. or		
		438/305.ccls. or 438/306.ccls.) or		.
		(438/585.ccls. or 438/592.ccls. or 438/595.ccls.)) and (MOSFET and		
		anisotropic\$4 and isotropic\$4 and etch\$3		
		anisotropics4 and isotropics4 and etch\$3 and tungsten and polysilicon)	-	
_	124		USPAT	2004/06/04 14:51
[123	438/301.ccls. or 438/303.ccls. or	55171	2004/00/04 14:51
		438/305.ccls. or 438/306.ccls.) or] .
		(438/585.ccls. or 438/592.ccls. or		
		438/595.ccls.)) and (MOSFET with (channel		
		adj length))		
-	10	MOSFET with (t-gate)	USPAT	2004/06/04 17:56
-	1558	438/301.ccls. or 438/303.ccls.	USPAT	2004/06/04 15:42
-	1499		USPAT	2004/06/04 15:42
-	814	438/197.ccls. or 438/299.ccls.	USPAT	2004/06/04 17:56
-	3139	438/197.ccls. or 438/299.ccls. or	USPAT	2004/06/04 17:56
1		438/301.ccls. or 438/303.ccls. or		
_	1236	438/305.ccls. or 438/306.ccls.	LICDAM	2004/06/04 17:56
	1236	(438/197.ccls. or 438/299.ccls. or 438/301.ccls. or 438/303.ccls. or	USPAT	2004/06/04 17:56
		438/305.ccls. or 438/306.ccls.) and MOSFET		
-	814	438/197.ccls. or 438/299.ccls.	USPAT	2004/06/04 17:56
-	934	((438/197.ccls. or 438/299.ccls. or	USPAT	2004/06/04 17:30
	- 	438/301.ccls. or 438/303.ccls. or		= 337, 33, 37 13, 31
		438/305.ccls. or 438/306.ccls.) and		
		MOSFET) not (438/197.ccls. or		
		438/299.ccls.)		
-	830	(((438/197.ccls. or 438/299.ccls. or	USPAT	2004/06/04 18:01
		438/301.ccls. or 438/303.ccls. or		
		438/305.ccls. or 438/306.ccls.) and		0
		MOSFET) not (438/197.ccls. or		
	10311	438/299.ccls.)) and channel MOSFET with channel	HCDATE	2004/06/04 10:00
-	1106	MOSFET with channel (gate and	USPAT USPAT	2004/06/04 18:08 2004/06/04 18:02
	1100	tungsten and polysilicon)	USFAI	2004/00/04 18:02
l -	10	((MOSFET with channel) and (gate and	USPAT	2004/06/04 18:02
	**	tungsten and polysilicon)) and (hydrogen	JULAI	2003/00/03 10.02
		adj bromide)		
-	122	(MOSFET with channel) and ((hydrogen adj	USPAT	2004/06/04 18:08
		bromide) or HBr)		
-	112	((MOSFET with channel) and ((hydrogen adj	USPAT	2004/06/04 18:08
		bromide) or HBr)) not (((MOSFET with		
		channel) and (gate and tungsten and		
		polysilicon)) and (hydrogen adj bromide))		
-	103	(((MOSFET with channel) and ((hydrogen adj	USPAT	2004/06/04 18:09
		bromide) or HBr)) not (((MOSFET with		
		channel) and (gate and tungsten and		
		polysilicon)) and (hydrogen adj bromide)))		
		<pre>and (((hydrogen adj bromide) or HBr) with etch\$3)</pre>		
		00011401	<u> </u>	<u> </u>